

OptiMOS® Power-Transistor

Feature

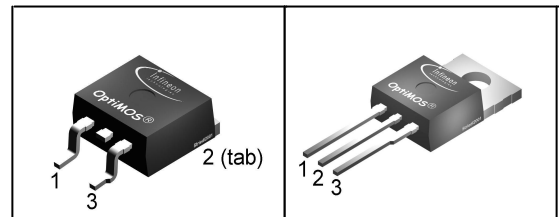
- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

Product Summary

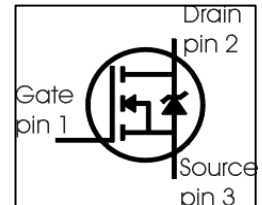
V_{DS}	75	V
$R_{DS(on)}$ max. SMD version	6.8	mΩ
I_D	80	A

P- TO263 -3-2

P- TO220 -3-1



Type	Package	Ordering Code	Marking
SPP80N08S2L-07	P- TO220 -3-1	Q67060-S6015	2N08L07
SPB80N08S2L-07	P- TO263 -3-2	Q67060-S6016	2N08L07



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current 1) $T_C=25\text{ °C}$	I_D	80 80	A
Pulsed drain current $T_C=25\text{ °C}$	$I_{D\text{ puls}}$	320	
Avalanche energy, single pulse $I_D=80\text{ A}$, $V_{DD}=25\text{ V}$, $R_{GS}=25\text{ Ω}$	E_{AS}	810	mJ
Repetitive avalanche energy, limited by $T_{jmax}^{2)}$	E_{AR}	30	
Reverse diode dv/dt $I_S=80\text{ A}$, $V_{DS}=60\text{ V}$, $di/dt=200\text{ A/μs}$, $T_{jmax}=175\text{ °C}$	dv/dt	6	kV/μs
Gate source voltage	V_{GS}	±20	V
Power dissipation $T_C=25\text{ °C}$	P_{tot}	300	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	0.3	0.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ³⁾	R_{thJA}	-	-	62 40	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	75	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=250\mu A$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=75V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=75V, V_{GS}=0V, T_j=125^\circ C^2)$	I_{DSS}	-	0.01 1	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	1	100	nA
Drain-source on-state resistance $V_{GS}=4.5V, I_D=67A$ $V_{GS}=4.5V, I_D=67A, \text{SMD version}$	$R_{DS(on)}$	-	6.5 6.2	9 8.7	$m\Omega$
Drain-source on-state resistance 4) $V_{GS}=10V, I_D=67A$ $V_{GS}=10V, I_D=67A, \text{SMD version}$	$R_{DS(on)}$	-	5.3 5	7.1 6.8	

¹Current limited by bondwire ; with an $R_{thJC} = 0.5K/W$ the chip is able to carry $I_D= 135A$ at $25^\circ C$, for detailed information see app.-note ANPS071E available at www.infineon.com/optimos

²Defined by design. Not subject to production test.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

⁴Diagrams are related to straight lead versions

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 80A$	74	148	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	5130	6820	pF
Output capacitance	C_{oss}		-	993	1320	
Reverse transfer capacitance	C_{rss}		-	415	620	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 40V$, $V_{GS} = 10V$, $I_D = 80A$, $R_G = 1.1\Omega$	-	25	38	ns
Rise time	t_r		-	81	122	
Turn-off delay time	$t_{d(off)}$		-	76	114	
Fall time	t_f		-	78	117	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 60V$, $I_D = 80A$	-	18	23	nC
Gate to drain charge	Q_{gd}		-	66	83	
Gate charge total	Q_g	$V_{DD} = 60V$, $I_D = 80A$, $V_{GS} = 0$ to $10V$	-	186	233	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 60V$, $I_D = 80A$	-	3.3	-	V

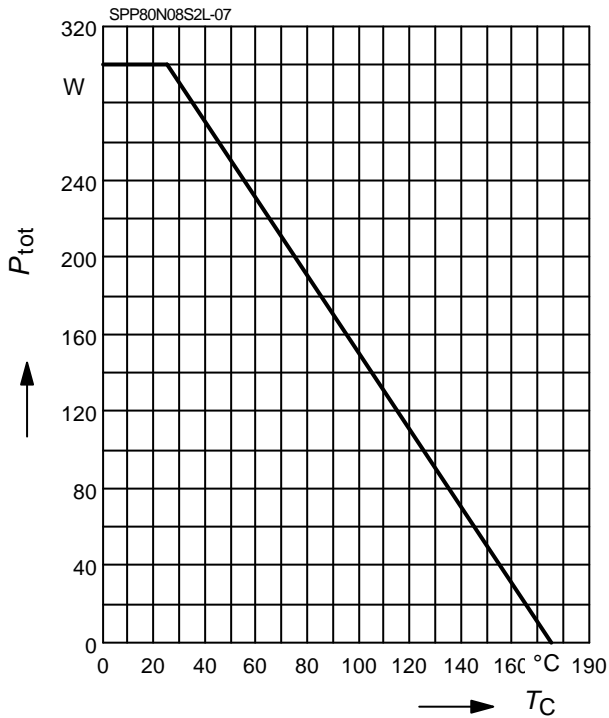
Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ C$	-	-	80	A
Inv. diode direct current, pulsed	I_{SM}		-	-	320	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V$, $I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 40V$, $I_F = I_S$, $di_F/dt = 100A/\mu s$	-	81	100	ns
Reverse recovery charge	Q_{rr}		-	197	250	

1 Power dissipation

$$P_{tot} = f(T_C)$$

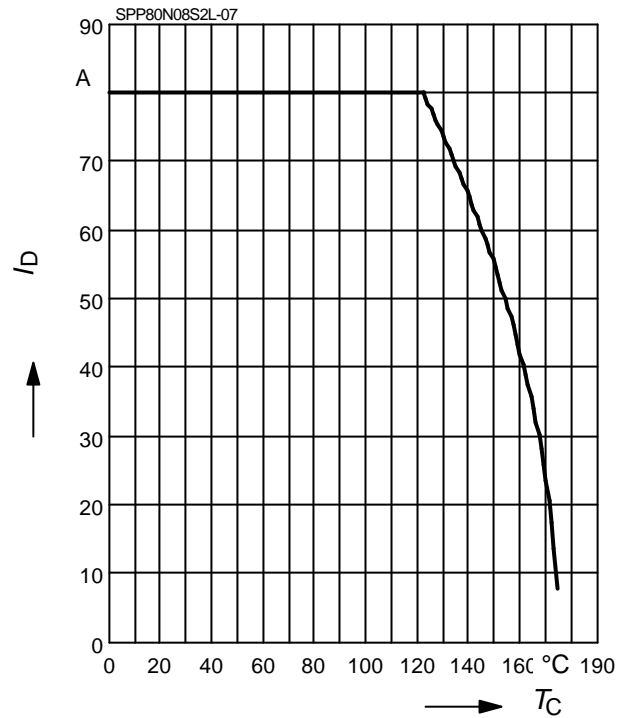
parameter: $V_{GS} \geq 4 \text{ V}$



2 Drain current

$$I_D = f(T_C)$$

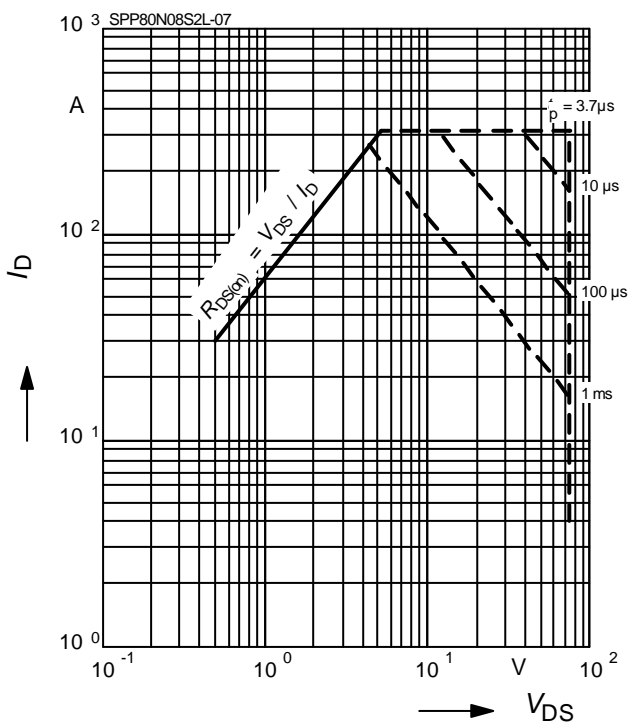
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

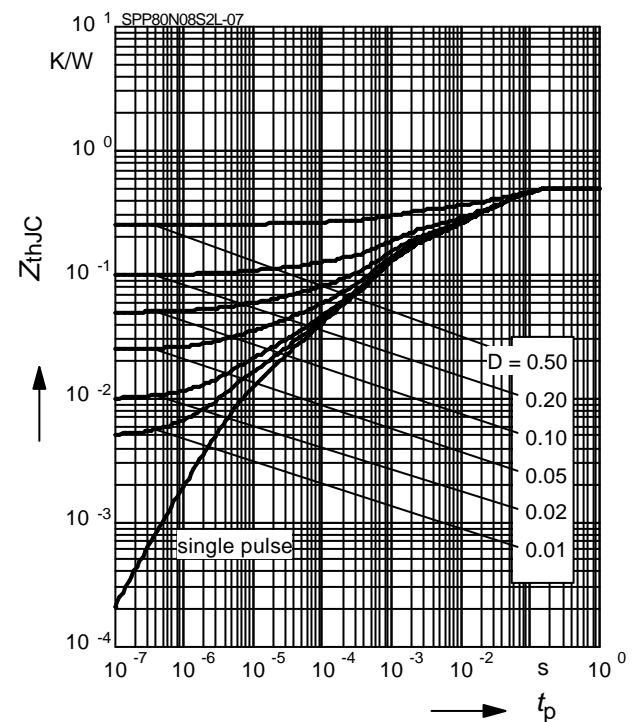
parameter: $D = 0.01$, $T_C = 25 \text{ °C}$



4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

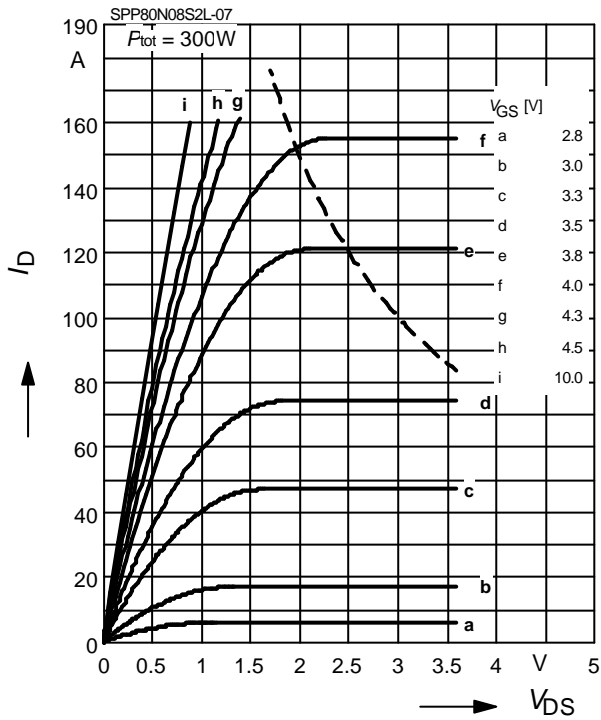
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$

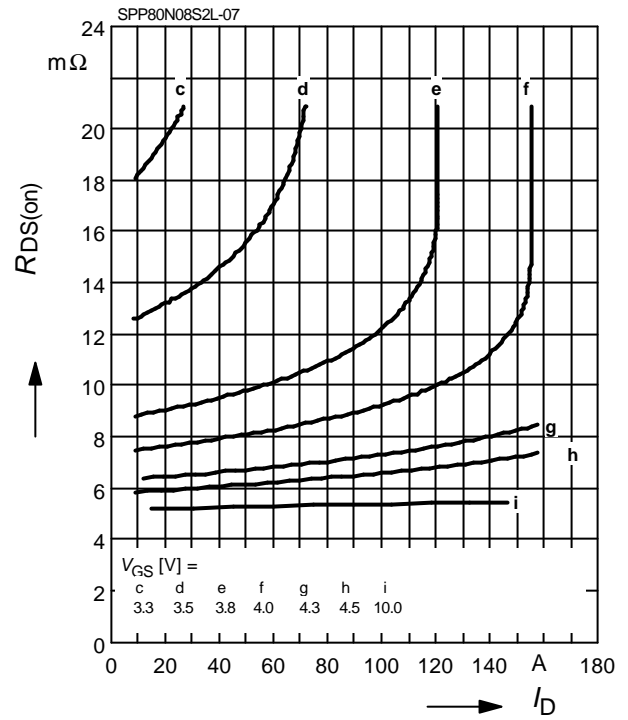
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(\text{on})} = f(I_D)$

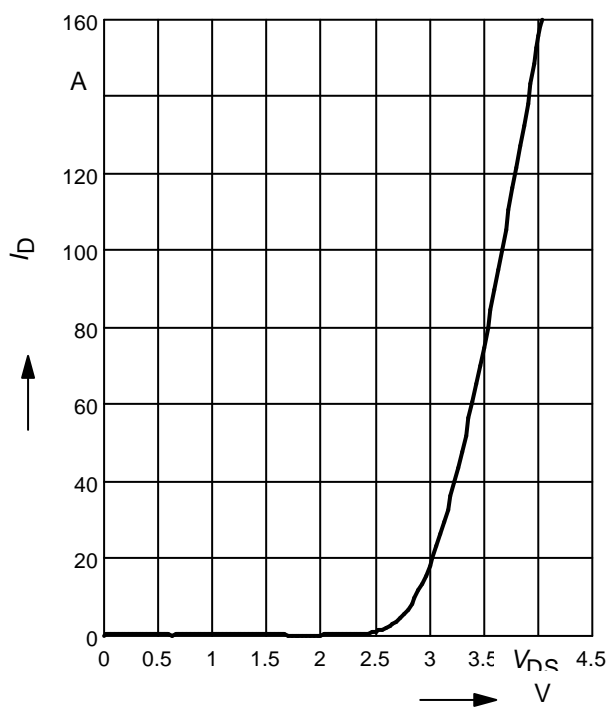
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(\text{on})\text{max}}$

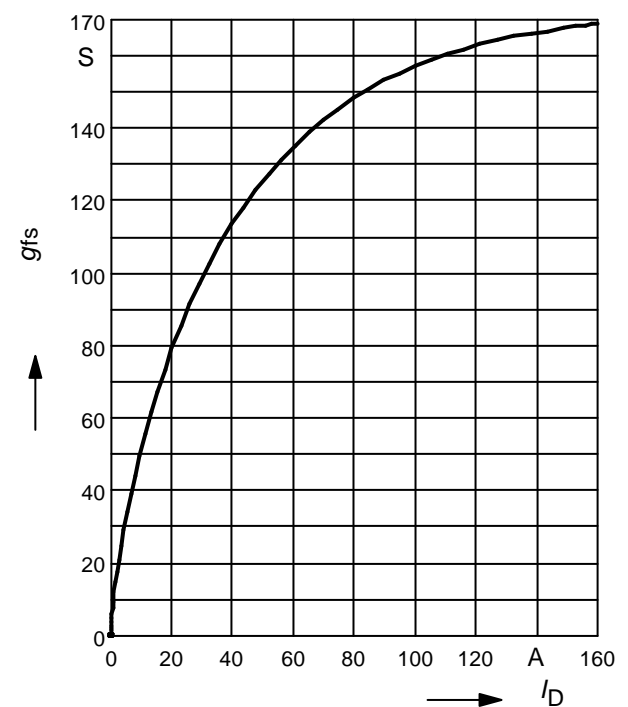
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$

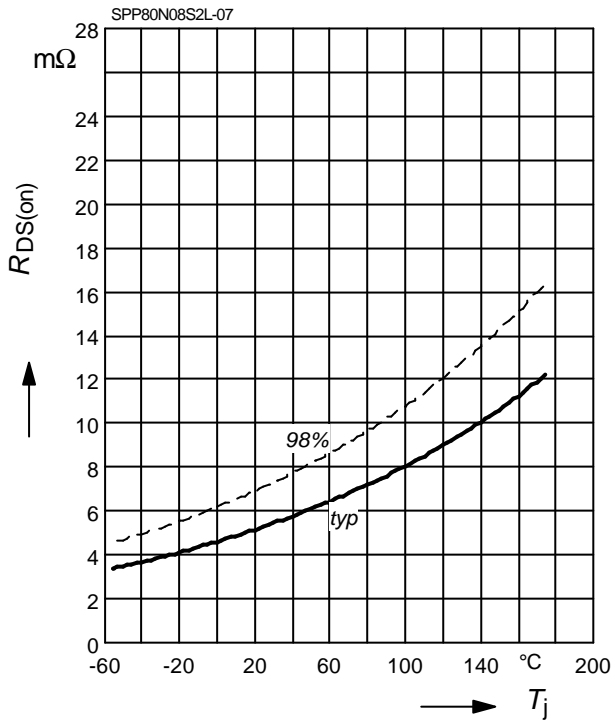
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

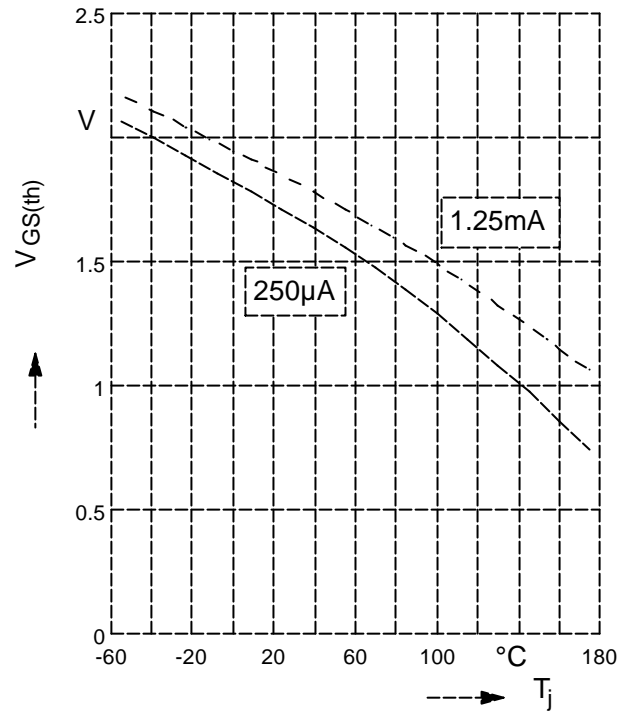
parameter : $I_D = 67\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

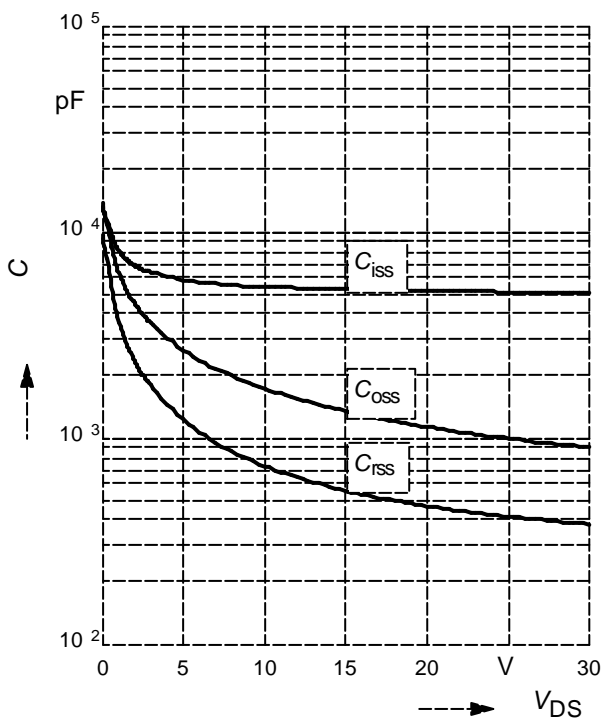
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

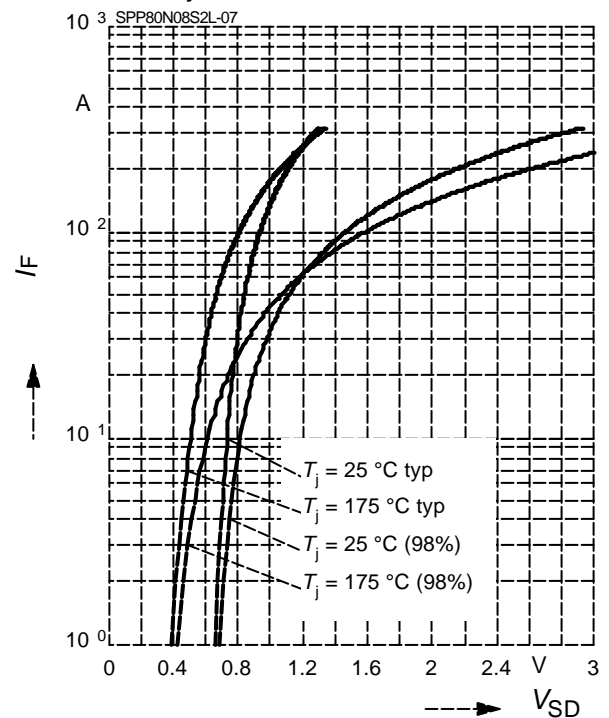
parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

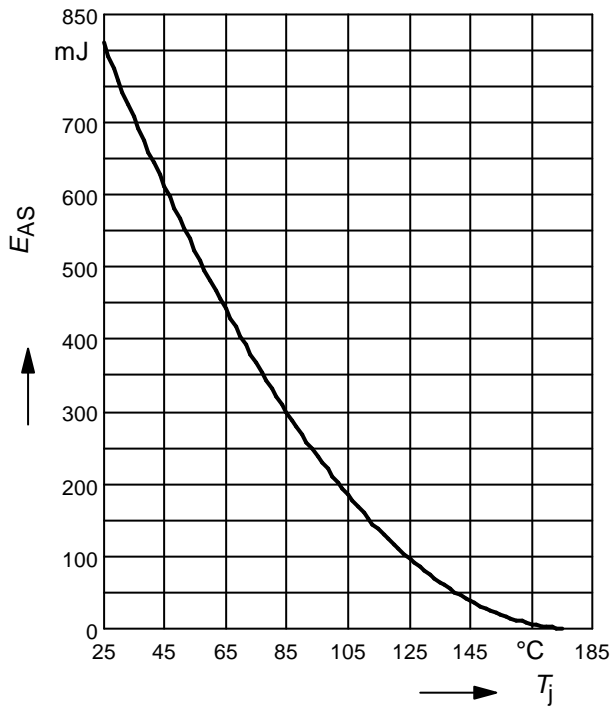
parameter: T_j , $t_p = 80\text{ µs}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

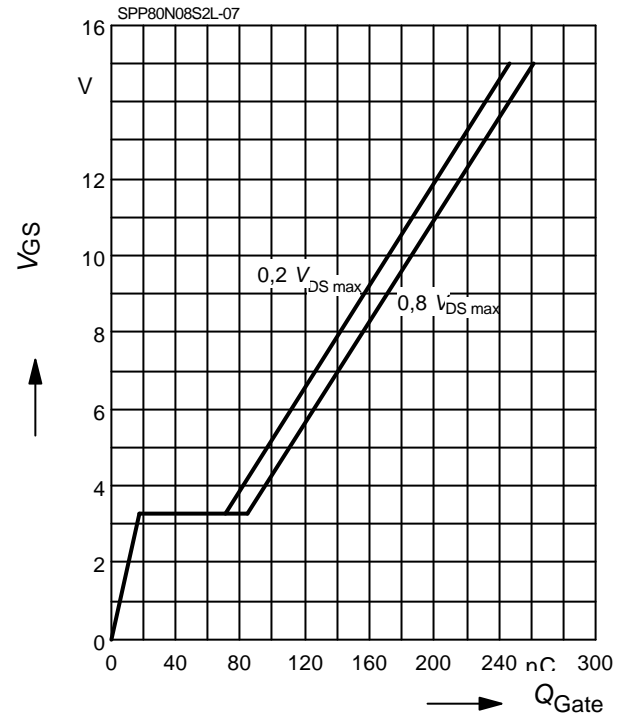
par.: $I_D = 80 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \Omega$



14 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

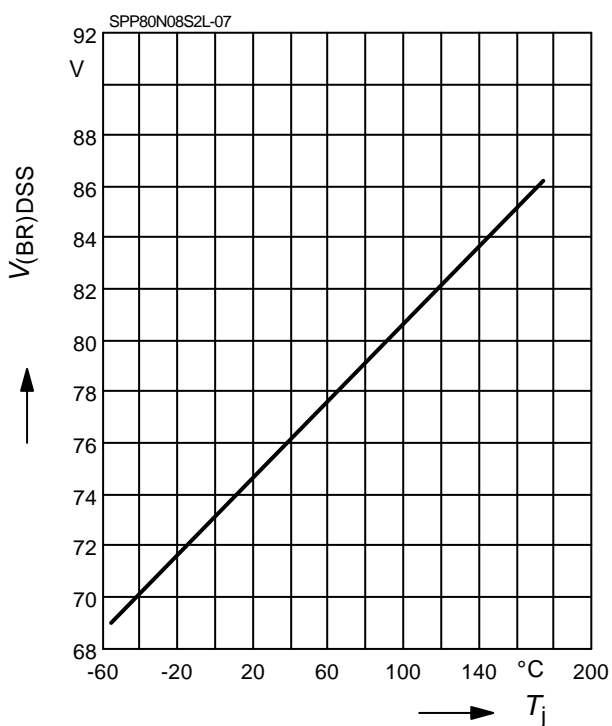
parameter: $I_D = 80 \text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter: $I_D = 10 \text{ mA}$



Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
© Infineon Technologies AG 1999
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Further information

Please notice that the part number is **BSPP80N08S2L-07** and **BSPB80N08S2L-07**, for simplicity the device is referred to by the term **SPP80N08S2L-07** and **SPB80N08S2L-07** throughout this documentation.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.